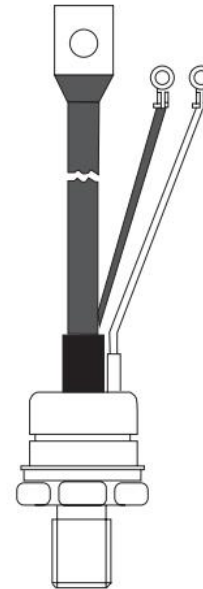


FEATURES

- Center amplifying gate
- Hermetic metal case with ceramic insulator
(Also available with glass-metal seal up to 1200 V)
- International standard case TO-209AB (TO-93)
- Compression Bonded Encapsulation for heavy duty operations such as severe thermal cycling
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RATINGS				UNIT
		ST180S04	ST180S08	ST180S12	ST180S16	
V_{RRM}	Repetitive Peak Reverse Voltage	400	800	1200	1600	V
V_{RSM}	Non-Repetitive Peak Reverse Voltage	400	800	1200	1600	V

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
$I_{T(AV)}$	Average Forward Current	$T_C=85^{\circ}\text{C}$, 180° conduction, half sine wave	200	A	
$I_{T(RMS)}$	Maximum RMS on-state current	DC at 76°C case temperature	360	A	
I_{TSM}	Max. peak, one-cycle forward, non-repetitive surge current	$t = 10\text{ms}$	No voltage reapplied	5700	A
		$t = 8.3\text{ms}$		5970	
		$t = 10\text{ms}$	100% V_{RRM} reapplied	4800	
		$t = 8.3\text{ms}$		5000	
T_J	Junction Temperature		-40~125	$^{\circ}\text{C}$	
T_{stg}	Storage Temperature Range		-40~150	$^{\circ}\text{C}$	

THERMAL CHARACTERISTICS

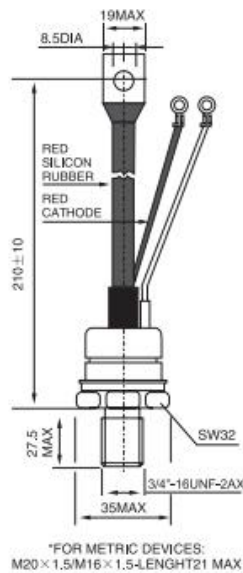
SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.105	°C/W

ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	TYPE	MAX	UNIT
V_{TM}	Forward Voltage Drop	$I_{pk} = 570\text{ A}$, $T_J = 125\text{ °C}$, $t_p = 10\text{ ms}$ sine pulse		1.75	V
I_{DRM} I_{RRM}	Max. peak reverse and off-state leakage current	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied		30	mA
I_{GT}	DC gate current required to trigger	$T_J = -40\text{ °C}$	180		mA
		$T_J = 25\text{ °C}$	90	150	
		$T_J = 125\text{ °C}$	40		
V_{GT}	DC gate voltage required to trigger	$T_J = -40\text{ °C}$	2.9		V
		$T_J = 25\text{ °C}$	1.8	3	
		$T_J = 125\text{ °C}$	1.2		
t_q	Typical turn-off time	$I_{TM} = 300\text{ A}$, $T_J = T_J$ max, $di/dt = 20\text{ A}/\mu\text{s}$, $V_R = 50\text{ V}$, $dv/dt = 20\text{ V}/\mu\text{s}$, Gate 0V 100 Ω , $t_p = 500\text{ }\mu\text{s}$		100	μs

PACKAGE OUTLINE

Dimensions in mm (1mm = 0.0394")



Case Style TO-93(ceramic)

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